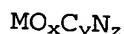


AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (original) A semiconductor device comprising a semiconductor substrate and a metal-compound film thereon, wherein the metal-compound film has a composition represented by the formula:



wherein x, y and z meet the conditions: $0 < x$, $0.1 \leq y \leq 1.25$, $0.01 \leq z$ and $x+y+z=2$; and M comprises at least Hf or Zr.

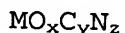
2. (original) the semiconductor device as claimed in Claim 1, wherein the formula further meets the conditions: $0.7 \leq x \leq 1.85$ and $0.05 \leq z \leq 0.2$.

3. (original) The semiconductor device as claimed in Claim 1, wherein the metal-compound film is formed by chemical vapor deposition.

4. (original) The semiconductor device as claimed in Claim 1, wherein the metal-compound film is formed by atomic layer deposition.

5. (original) A semiconductor device comprising a semiconductor substrate, a pair of electrodes thereon and a

capacitor comprising a dielectric film between the electrodes, wherein the dielectric film comprises a metal-compound film having a composition represented by the formula:



wherein x, y and z meet the conditions: $0 < x$, $0.1 \leq y \leq 1.25$, $0.01 \leq z$ and $x+y+z=2$; and M comprises at least Hf or Zr.

6. (original) The semiconductor device as claimed in Claim 5, wherein said pair of electrodes comprise one or more of metal-compound selected from the group consisting of TiN, Ti, TaN, Ta, W, WN, Pt, Ir and Ru.

7. (original) The semiconductor device as claimed in Claim 5, wherein said pair of electrodes comprise TiN.

8. (original) The semiconductor device as claimed in Claim 5, wherein the thickness of said pair of electrodes is 5 to 40 nm.

9. (original) The semiconductor device as claimed in Claim 5, further comprising a gate electrode formed on the semiconductor substrate; a transistor comprising:

a source and a drain regions formed in the semiconductor substrate whose surfaces are silicided; and

a connecting plug for connecting the source and the drain regions in the transistor with the capacitor.

10. (original) A semiconductor device comprising a semiconductor substrate; a gate insulating film formed on the main surface of the semiconductor substrate; a gate electrode on the gate insulating film; and a source and a drain regions formed on the semiconductor substrate which together sandwich the gate electrode,

wherein the gate insulating film comprises a metal-compound film having a composition represented by the formula:



wherein x, y and z meet the conditions: $0 < x$, $0.1 \leq y \leq 1.25$, $0.01 \leq z$ and $x+y+z=2$; and M comprises at least Hf or Zr.

11-20. (canceled)